

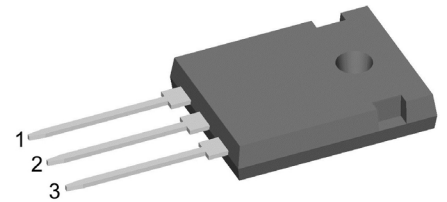
SiC Schottky Diode

$$V_{RRM} = 1200 \text{ V}$$

$$I_{FAV} = 2 \times 18.5 \text{ A}$$

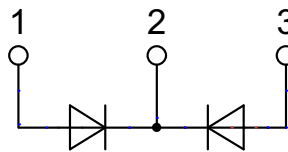
Ultra fast switching
 Zero reverse recovery
 Common Cathode

Part number
DCG35C1200HR



Backside: isolated

 E72873



Features / Advantages:

- Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive temperature coefficient of forward voltage
- $T_{VJM} = 175^{\circ}\text{C}$

Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

Package: ISO247

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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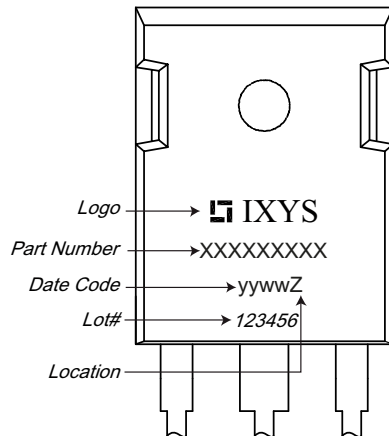


SiC Diode (per diode)				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V _{RSM}	max. non-repetitive reverse blocking voltage					1200	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 175°C		35 65	200 400	μA μA
V _F	forward voltage	I _F = 20 A	T _{VJ} = 25°C		1.5	1.8	V
		I _F = 40 A		V			
		I _F = 20 A	T _{VJ} = 175°C		2.2	3.0	V
		I _F = 40 A		V			
I _{FAV}	average forward current	T _C = 80°C } rectangular, d = 0.5				18.5	A
		T _C = 100°C } T _{VJ} = 175°C				17.0	A
I _{F25}	forward current	based on typ. V _{F0} and r _F		T _C = 25°C		34	A
I _{F80}				T _C = 80°C		26.5	A
I _{F100}				T _C = 100°C		23	A
I _{FSM}	max forward surge current	t = 10 ms, half sine (50 Hz)	T _{VJ} = 25°C V _R = 0V				A
		t _p = 10 μs, pulse			1000	A	
V _{F0}	threshold voltage	} for power loss calculation	T _{VJ} = 125°C		0.78		V
r _F	slope resistance		175°C		0.73		V
			T _{VJ} = 125°C		57.0		mΩ
			175°C		70.5		mΩ
Q _C	total capacitive charge	V _R = 800 V, I _F = 20A dI/dt = 200 A/μs	T _{VJ} = 25°C		99		nC
C	total capacitance	V _R = 0 V V _R = 400 V V _R = 800 V	T _{VJ} = 25°C, f = 1 MHz		1500		pF
					93		pF
					67		pF
R _{thJC}	thermal resistance junction to case	with heatsink compound; IXYS test setup				1.4	K/W
R _{thJH}	thermal resistance junction to heatsink				1.6		K/W



Package ISO247				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I _{RMS}	RMS current	per terminal				70	A
T _{stg}	storage temperature			-40		150	°C
T _{op}	operation temperature			-40		150	°C
T _{VJ}	virtual junction temperature			-40		175	°C
Weight					6		g
M _D	mounting torque			0.8		1.2	Nm
F _C	mounting force with clip			40		120	N
d _{Spp/App}	creepage distance on surface /	terminal to terminal		2.7			mm
d _{Spb/Apb}	striking distance through air	terminal to backside		4.1			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz; RMS; I _{ISOL} < 1 mA		3600		V
		t = 1 minute			3000		V

Product Marking



Part description

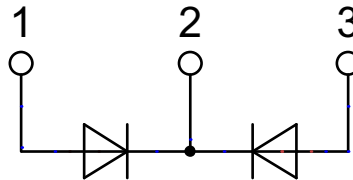
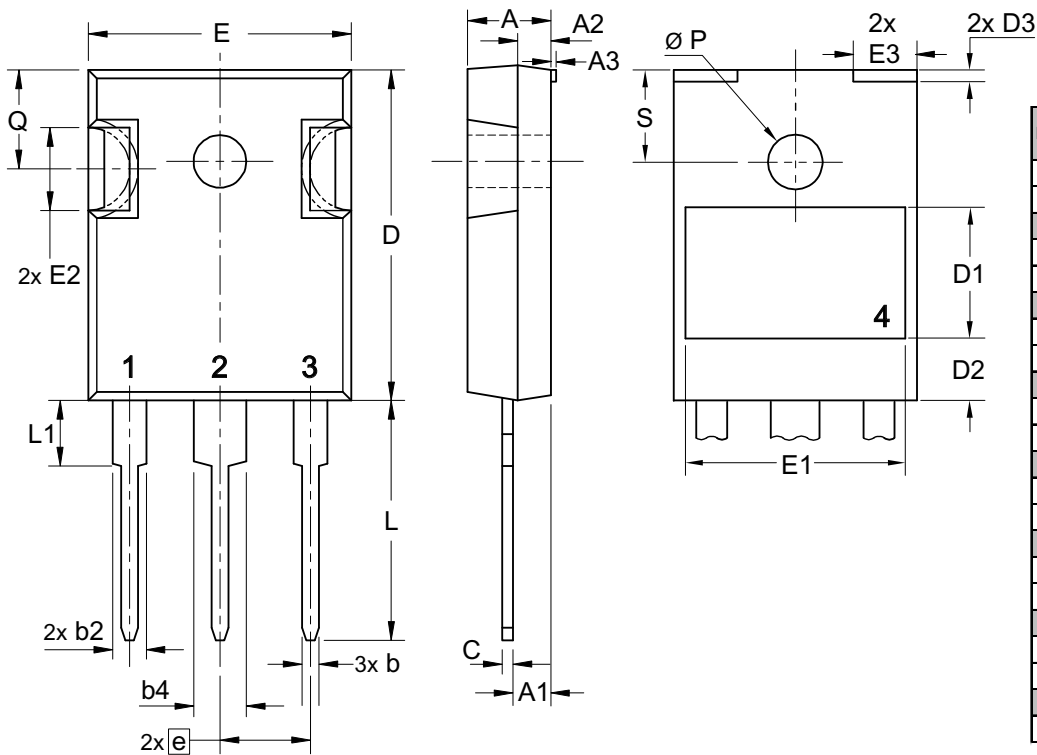
D = Diode
 C = SiC
 G = Extreme fast
 35 = Current Rating [A]
 C = Common Cathode
 1200 = Reverse Voltage [V]
 HR = ISO247 (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG35C1200HR	DCG35C1200HR	Tube	30	DCG35C1200HR

Equivalent Circuits for Simulation *on die level, typical

		$T_{VJ} = 125^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$	
$V_{0\max}$	threshold voltage	0.78	0.73	V
$R_{0\max}$	slope resistance *	57.0	70.5	mΩ

Outlines ISO247



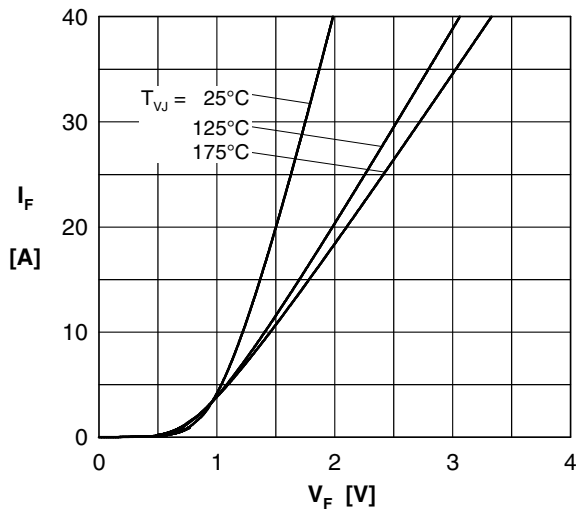
SiC Diode (per diode)


Fig. 1 Typ. forward characteristics.

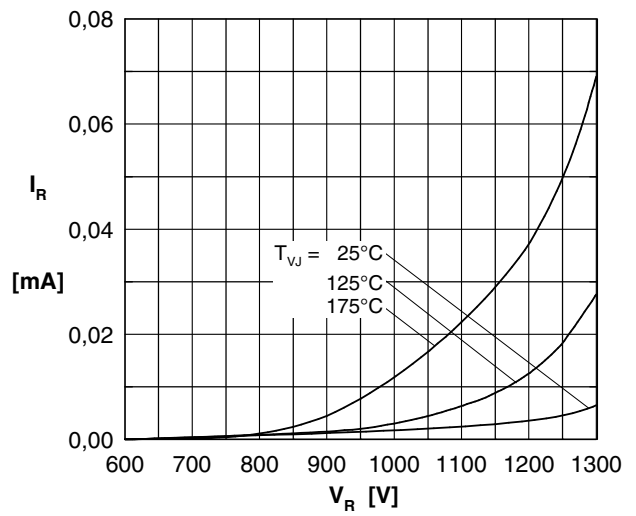


Fig. 2 Typ. reverse characteristics

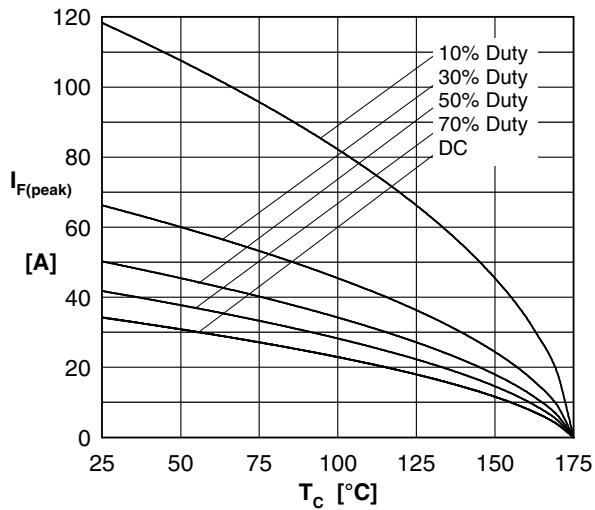


Fig. 3 Typ. current derating

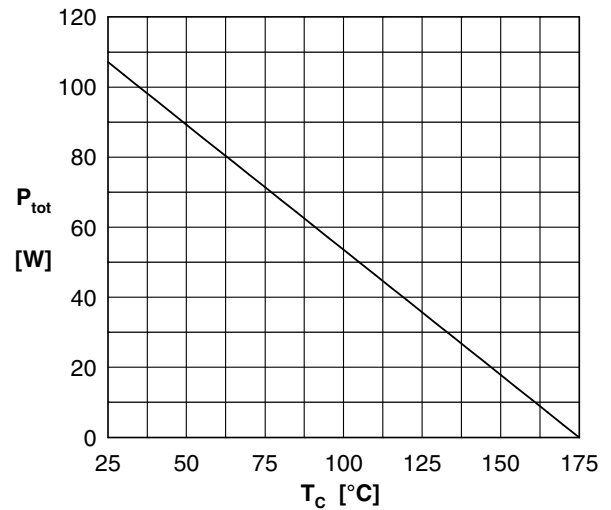


Fig. 4 Power derating

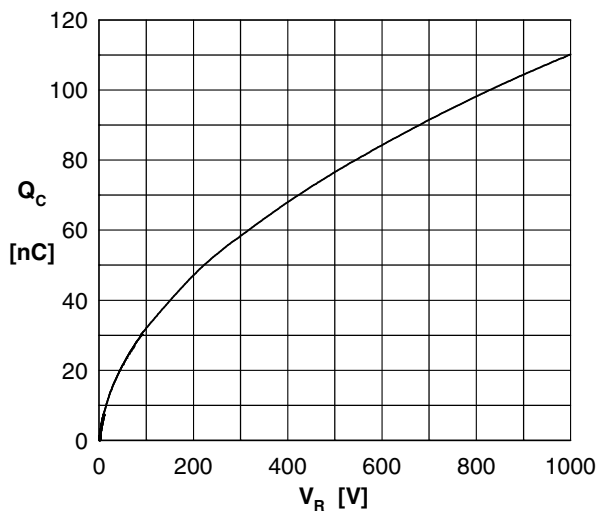


Fig. 5 Typ. recovery charge vs. reverse voltage

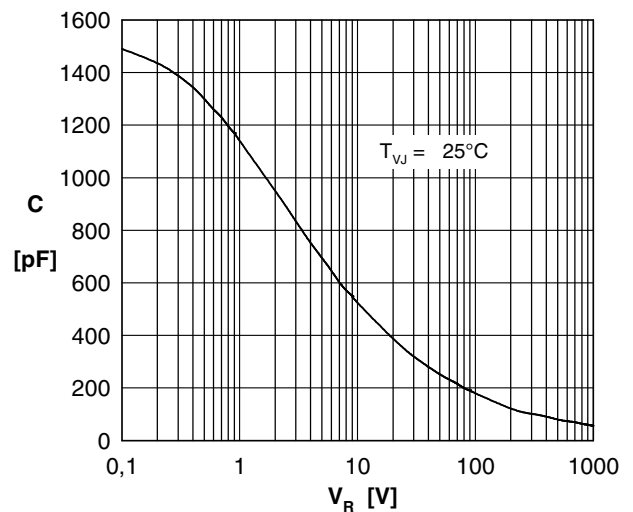


Fig. 6 Typ. junction capacitance vs. reverse Voltage

SiC Diode (per diode)

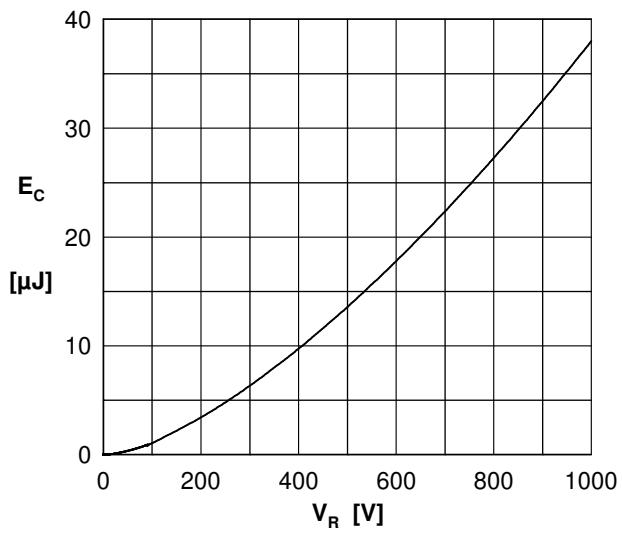


Fig. 7 Typical capacitance stored energy

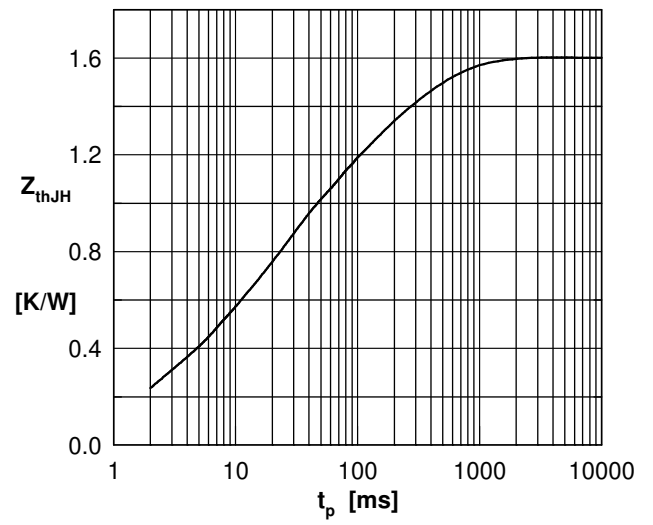


Fig. 8 Typ. transient thermal impedance
junction to heatsink